

A central role for the exchange-correlation hole in the 2D metal-insulator transition

D.J.W. Geldart^{*,†}, D. Neilson^{*}, and J.S. Thakur^{*}

^{*} *School of Physics, The University of New South Wales, Sydney 2052 Australia*

[†] *Department of Physics, Dalhousie University, Halifax, NS, Canada B3H3J5*

The 2D metal-insulator transition can be induced either by decreasing the carrier density or by increasing the spin polarization by applying a magnetic field parallel to the plane. Using experimental results for the shift in critical carrier density in an applied field, we show that the two-electron pair correlation function at short distance ($k_F r \lesssim 2$) has a universal form along the transition line in the magnetic field-carrier density plane. This result provides direct evidence of the central role of Coulomb repulsion and the exchange-correlation hole in driving the metal-insulator transition.

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The metal-insulator transition is a problem of great current interest¹. In spite of intense investigation there is still no consensus on understanding the basic features of the problem and there is no microscopic theory. It is therefore useful to investigate phenomenological aspects of the metal-insulator transition. In this paper we point out an interesting empirical relationship between the dependence of the 2D pair correlation function $g(\mathbf{r})$ on a magnetic field parallel to the plane of a two dimensional electron liquid and the freezing line in the phase diagram of the metal-insulator transition.

It is possible to regard the transition from the metallic state to an insulating state as a special case of freezing of the electron liquid. Phenomenological criteria in terms of pair correlation functions and static structure factors for the freezing of both classical and quantum liquids in the absence of impurities have been known for some time. The properties of the static structure factor $S(\mathbf{k})$ near freezing show common features along the freezing line for a wide class of 3D interacting systems, and equivalent statements can be made in terms of the correlation function $g(\mathbf{r}) = 1 + \int d^3\mathbf{k}/(2\pi)^3 e^{i\mathbf{k}\cdot\mathbf{r}}\{S(\mathbf{k}) - 1\}$. Hansen and Verlet² established for systems of particles interacting through a Lennard-Jones potential in three dimensions that the Lindemann ratio along the melting line in the temperature-density plane is practically constant along the melting line. Hansen and Verlet also showed that on approaching the transition from the liquid state, the amplitude of the main peak in the static structure factor $S(\mathbf{k})$ is very nearly constant $\sim 2.85 \pm 0.1$ along the crystallization line. This same value has been found for the peak in $S(\mathbf{k})$ along the crystallization line for both classical one component plasmas and systems of classical hard spheres³. Adler and Wainwright⁴ obtained analogous results for two dimensional systems of hard discs. Generalizations of these ideas to quantum systems have been given, although the extra role of zero point motion makes the effect less clear-cut⁵. The essential point is that conditions for crystallization of the system as a function of external parameters correspond to critical values for short distance properties of the pair correlation function, or correspondingly the static structure factor. Consequently, insight into the freezing mechanism may be obtained by studying short distance properties of pair correlation functions as parameters are varied in the vicinity of the transition. This is clearly simpler than an explicit calculation of the equation of state, specifying full details of the system and its interactions. This can be useful for gaining phenomenological understanding in the absence of a microscopic theory.

This characterization of the freezing line in terms of the strength of short distance correlations has been developed for pure systems for which the density distribution is uniform. The electron distribution in the systems exhibiting a metal-insulator transition is nonuniform but since the transition is observed at low levels of impurities, the short distance $g(\mathbf{r})$

for $k_F r < 2$ should be well approximated by the corresponding function for the pure system. Diffusion quantum Monte Carlo (DQMC) simulations^{6,7} give us the ground state properties of the 2D system without impurities including $g(\mathbf{r})$. For the pure system the transition from liquid to solid occurs at extremely low densities corresponding to $r_s = 37 \pm 5$, where r_s is the average electron spacing in effective Bohr radii. The preliminary quantum Monte Carlo calculations of Chui and Tanatar⁸ which include the effect of charged impurities have suggested that impurities may stabilize a solid ground state at densities as high as $r_s = 10$. Although a precise value of r_s for the transition was not determined, this result does indicate that low levels of static defects in the form of a weak quasi-random potential may facilitate solidification.

The metal-insulator transition occurs in very high mobility quasi-2D semiconductor devices with low carrier densities, $r_s \gtrsim 5$, (although very recently Altshuler *et al*⁹ have discussed data suggesting that the phenomenon may persist up to densities as high as $r_s \simeq 2$). At the very low densities of the Wigner crystal, $r_s \gtrsim 37$, the strong electron correlations generate a large area of near-zero electron density surrounding each electron⁶. This repulsive hard core region forms part of the electron's exchange-correlation hole, the complete density profile of which is known from the DQMC $g(\mathbf{r})$.⁶ The results in Ref. 6 establish that the radius of the exchange-correlation hole shrinks as the electron density is increased above the solidification density $r_s \simeq 37$. However, the hard core effect persists in the electron liquid up to a density corresponding to $r_s \simeq 7$. This is a factor some 25 times greater than the density at the Wigner transition.

The DQMC numerical simulations in Refs. 6, 7 show that the exchange-correlation hole is stronger for spin polarized electrons than for unpolarized electrons. This is due to the additional exchange acting between the increased proportion of parallel spin electrons. In Fig. 1 we see that polarizing the spins at a fixed density corresponding to $r_s = 9$ significantly expands the relative area of the hard core region in $g(\mathbf{r})$. By $r_s = 7$ the region of zero density around each electron has disappeared for the unpolarized system, but for the polarized system at the same density it is still present.

We have proposed¹⁰ that the reported suppression of the metallic state by a parallel magnetic field^{11,12}, is directly associated with the expansion of the area of the hard core caused by the partial alignment of the spins in the magnetic field. We found that fields $H_{\parallel} < 1$ T destabilize the metallic phase. The enhancement in the exchange means that the critical impurity density n_i^c at the transition for the polarized system is smaller than the n_i^c for the unpolarized system at the same carrier density.

Hamilton *et al*¹¹ reported that the metal-insulator transition boundary in *p*-GaAs is shifted by a parallel field $H_{\parallel} = 0.6$ T from hole density $p_s = 7.5 \times 10^{10} \text{ cm}^{-2}$ to $p_s = 12.4 \times 10^{10} \text{ cm}^{-2}$, or correspondingly, from $r_s = 9$ to $r_s = 7$. This is shown in Fig. 2. The transition boundary gives the critical magnetic field $H_c(r_s)$ as a function of carrier density. Moving along the boundary in the direction of increasing density, the value of H_c increases, thus increasing the alignment of the electron spins.

We connect magnetic field and spin polarization by estimating the degree of polarization as a function of a parallel magnetic field $H_{\parallel}$ using DQMC data for the pure electron system taken from Rapisarda and Senatore⁷. In Fig. 3 we show the critical H_c needed to fully polarize the electron spins, determined by equating the Zeeman energy gain to the energy difference, $(g\mu_B/\hbar)H_c(r_s) = [E_p(r_s) - E_u(r_s)]$, where $E_p(r_s)$ and $E_u(r_s)$ are the energies per electron for the fully spin polarized and unpolarized states, respectively. We take $(g\sigma_z) = 1.1$ for GaAs¹³. For fields $H_{\parallel} < H_c(r_s)$ we use a linear relation to determine the degree of polarization. At $r_s = 7$ a field $H_{\parallel} = 0.6$ T induces 50% spin polarization.

We emphasize that the pair correlation function in the vicinity of the transition is not expected to be significantly affected at short distances by low levels of disorder. For this reason the DQMC $g(\mathbf{r})$ for the defect free system can be used for the short ranged pair correlation function at the transition. Our main result is shown in Fig. 4 where we see for $k_F r \leq 2$ that the $g(\mathbf{r})$ on the transition boundary remains fixed all the way along the observed transition line. This indicates that for a given sample the transition is determined by a fixed functional form of the short-range $g(\mathbf{r})$, and is equivalent to a critical density profile of the exchange-correlation hole. The fixed functional form for $g(\mathbf{r}) = g(\mathbf{r}, H_c(r_s))$ suggests a fixed

functional form for $S(\mathbf{k})$. This is reminiscent of the role of $S(\mathbf{k})$ in characterizing the phase boundary in a wide range of liquid-“solid” transitions. It indicates that the metal-insulator transition is driven by electron-electron interactions and suggests that the transition is an intrinsic many-electron effect and not an artefact of material dependent properties.

We conclude that the metal-insulator boundary for the sample as a function of spin polarization and carrier density is determined by a fixed functional form of the two-electron correlation function at short distances. By defining an exchange-correlation hole radius r_c as the value of r at which $g(\mathbf{r})$ exceeds a fixed value $\ll 1$ such as 0.01, then along the transition line as a function of parallel magnetic field H and carrier density ρ we have,

$$\frac{\partial r_c}{\partial \rho} \delta \rho + \frac{\partial r_c}{\partial H} \delta H = 0 . \quad (1)$$

This means that a knowledge of the dependence of $g(\mathbf{r})$ on ρ and H permits us to predict the value of the gradient $\partial H_c / \partial \rho|_{crit-line}$ of the phase boundary.

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FIGURES

FIG. 1. Two-electron correlation function $g(\mathbf{r})$ taken from Ref. 6 at $r_s = 9$ for unpolarized system (dotted line) and fully polarized system (dashed line), showing the effect of exchange enhancement.

FIG. 2. Plot of phase boundary of metal-insulator transition as a function of parallel magnetic field and carrier density r_s taken from Ref. 11.

FIG. 3. Critical parallel magnetic field H_c as a function of r_s .

FIG. 4. Correlation function $g(\mathbf{r})$ along the observed metal-insulator transition boundary. Dotted line: $r_s = 9$, unpolarized. Dash-dot line: $r_s = 8$ for $H_{\parallel} = 0.4$ T. Dashed line: $r_s = 7$ for $H_{\parallel} = 0.6$ T. The three curves are essentially identical, indicating a universality of the short range correlations at the transition.







